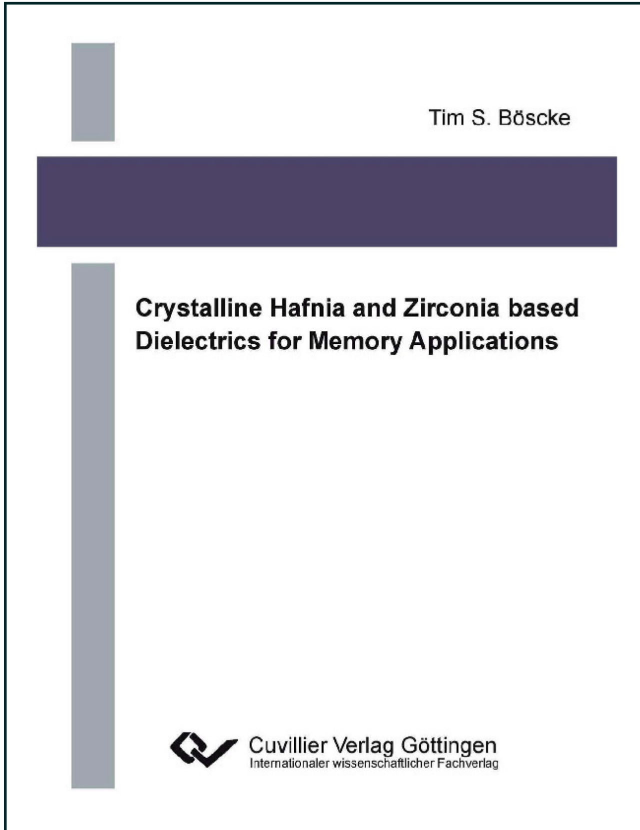
Tim S. Böscke (Autor)

Crystalline Hafnia and Zirconia based Dielectrics for Memory Applications



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